AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) A method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer, the method comprising:

applying an adhesive film to a circuit-formed surface of a semiconductor wafer, the adhesive film comprising an adhesive layer formed on one surface of a base film, the base film comprising at least one film layer having a gas transmission rate of not more than 49.35 ml/m^2·day/MPa wherein the film layer having a gas transmission rate of not more than 49.35 ml/m^2·day/MPa is an outermost layer of the base film on the side on which the adhesive layer is not formed; and

forming a metal film on the non-circuit-formed surface of the semiconductor wafer to which the adhesive film is applied.

2. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 1, wherein the film layer having a gas transmission rate of not more than 49.35 ml/m^2·day/MPa comprises a metal film layer or a metal oxide film layer.

3. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 1, wherein the base film comprises at least one film layer having a gas transmission rate of not more than 9.87 ml/m^2·day/MPa and water absorptance of not more than 1.0 weight %.

4. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 1, wherein the base film further comprises one film layer selected from an ethylene-vinyl acetate copolymer film, a polyester film and a polyethylene film.

5. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 1, wherein the adhesive layer has a storage elastic modulus of not less than 1×10^5 Pa at 150°C.

6. (Currently Amended) An adhesive film for forming a metal film on a non-circuit-formed surface of a semiconductor wafer, comprising an adhesive layer formed on one surface of a base film, the base film comprising at least one film layer having a gas transmission rate of not more than 49.35 ml/m^2·day/MPa wherein the film layer having a gas transmission rate of not more than 49.35 ml/m^2·day/MPa is an outermost layer of the base film on the side on which the adhesive layer is not formed.

7. (Previously Presented) An adhesive film for forming a metal film on a non-circuit-formed surface of a semiconductor wafer, comprising an adhesive layer formed on one surface of a base film, the base film comprising at least one film layer having a gas transmission rate of not more than 9.87 ml/m^2·day/MPa and water absorptance of not more than 1.0 weight %, wherein the film layer having a gas transmission rate of not more than 49.35 ml/m^2·day/MPa is an outermost layer of the base film on the side on which the adhesive layer is not formed.

8. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 2, wherein the base film further comprises one film layer selected from an ethylene-vinyl acetate copolymer film, a polyester film and a polyethylene film.

9. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 3, wherein the base film further comprises one film layer selected from an ethylene-vinyl acetate copolymer film, a polyester film and a polyethylene film.

10. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 2, wherein the adhesive layer has a storage elastic modulus of not less than 1×10^5 Pa at 150°C.

11. (Previously Presented) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 3, wherein the adhesive layer has a storage elastic modulus of not less than 1×10^5 Pa at 150°C.

12. (Canceled)

13. (Currently Amended) The method for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 2, wherein the metal film layer or the metal oxide film layer ~~is the outermost layer of the base film at the side the adhesive film is not formed~~ the outermost layer of a side of the base film, the side of the base film being a side on which the adhesive layer is not formed.

14. (Currently Amended) The adhesive film for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim **[[**10**]]** 6, wherein the film layer is the layer having a gas transmission rate of not more than 49.35 $ml/m^2 \cdot day/MPa$ and comprises a metal film layer or a metal oxide film layer.

15. (Canceled)

16. (Currently Amended) The adhesive film for forming a metal film on a non-circuit-formed surface of a semiconductor wafer according to claim 14, wherein the metal film layer or the metal oxide film layer is ~~the outermost layer of the base film at the side the adhesive film is not formed~~ the outermost layer of a side of the base film, the side of the base film being a side on which the adhesive layer is not formed.